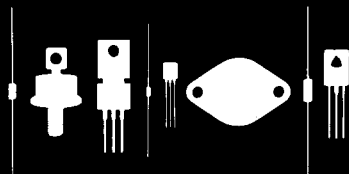


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145 Adams Avenue
Hauppauge, New York 11788



2N3119

NPN SILICON TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3119 type is a silicon NPN transistor manufactured by the epitaxial planar process designed for high voltage switching applications.

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage (V _{BE} =1.5V)	V _{CEV}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EB0}	4.0	V
Collector Current	I _C	0.5	A
Power Dissipation	P _D	1.0	W
Power Dissipation (T _C =25°C)	P _D	4.0	W
Operating and Storage Junction Temperature	T _J , T _{STG}	-65 TO +200	°C

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{CB0}	V _{CB} =60V		50	nA
I _{CB0}	V _{CB} =60V, T _A =150°C		50	μA
I _{EB0}	V _{BE} =3.0V		100	nA
BV _{CB0}	I _C =0.1mA	100		V
BV _{CEV}	I _C =0.1mA, V _{BE} =1.5V	100		V
BV _{CEO}	I _C =10mA	80		V
BV _{EB0}	I _E =0.1mA	4.0		V
V _{CE} (SAT)	I _C =100mA, I _B =10mA		0.5	V
V _{BE} (SAT)	I _C =100mA, I _B =10mA		1.1	V
h _{FE}	V _{CE} =10V, I _C =10mA	40	-	
h _{FE}	V _{CE} =10V, I _C =100mA	50	200	
h _{FE}	V _{CE} =10V, I _C =250mA	20	-	
f _T	V _{CE} =28V, I _C =25mA, f=50MHz	250		MHz
C _{ob}	V _{CB} =28V, I _C =0, f=1.0MHz		6.0	pF
t _{ON}	V _{CC} =28V, I _C =100mA, I _{B1} =10mA		40	ns
t _{OFF}	V _{CC} =28V, I _C =100mA, I _{B2} =10mA		700	ns

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